



#### 100V HALF-BRIDGE GATE DRIVER IN W-DFN3030-10

### **Description**

The DIODES™ DGD0503 is a high-voltage, high-speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half-bridge configuration. High voltage processing techniques enable the DGD0503's high side to switch to 100V in a bootstrap operation.

The DGD0503 logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver output features high pulse current buffers designed for minimum driver cross conduction. DGD0503 has a fixed internal deadtime of 430ns (typical).

The DGD0503 is offered in the W-DFN3030-10 (Type TH) package and operates over an extended -40°C to +125°C temperature range.

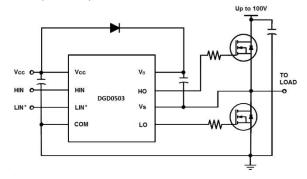
#### **Features**

- Floating High-Side Driver in Bootstrap Operation to 100V
- Drives Two N-Channel MOSFETs or IGBTs in a Half-Bridge Configuration
- 290mA Source/600mA Sink Output Current Capability
- Outputs Tolerant to Negative Transients
- Internal Dead Time of 430ns to Protect MOSFETs
- Wide Low-Side Gate Driver Supply Voltage: 10V to 20V
- Logic Input (HIN and LIN\*) 3.3V Capability
- Schmitt Triggered Logic Inputs
- Undervoltage Lockout for Vcc (Logic and Low-Side Supply)
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

### **Applications**

- DC-DC converters
- DC-AC inverters
- AC-DC power supplies
- Motor controls
- Class-D power amplifiers



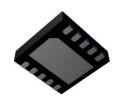
**Typical Configuration** 

### **Mechanical Data**

- Package: W-DFN3030-10
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish Matte Tin Finish Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.017 grams (Approximate)







**Bottom View** 

W-DFN3030-10 (Type TH)

### Ordering Information (Note 4)

Part Number	Dookogo	Marking	Reel Size (inches)	Tape Width (mm)	Packing	
Part Number	Package		neer Size (iliches)	rape widii (iiiii)	Qty.	Carrier
DGD0503FN-7	W-DFN3030-10 (Type TH)	DGD0503	7	8	3,000	Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>
  4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**



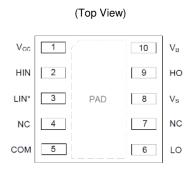
DGD0503 = Product Type Marking Code YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

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# Pin Diagrams

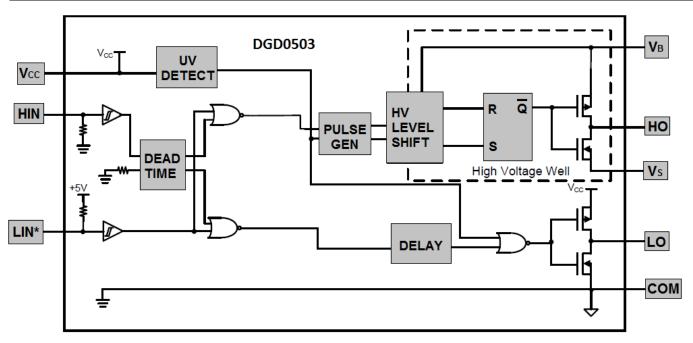


W-DFN3030-10 (Type TH)

# **Pin Descriptions**

Pin Number	Pin Name	Function
1	Vcc	Logic and Low-Side Supply
2	HIN	Logic Input for High-Side Gate Driver Output in Phase with HO
3	LIN*	Logic Input for Low-Side Gate Driver Output out of Phase with LO
4, 7	NC	No Connection (No Internal Connection)
5	COM	Low-Side and Logic Return
6	LO	Low-Side Gate Drive Output
8	Vs	High-Side Floating Supply Return
9	НО	High-Side Gate Drive Output
10	V <sub>B</sub>	High-Side Floating Supply
PAD	Substrate	Connect to COM on PCB

# **Functional Block Diagram**





## **Absolute Maximum Ratings** (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Supply Voltage	V <sub>B</sub>	-0.3 to +124	V
High-Side Floating Supply Offset Voltage	Vs	$V_B - 24$ to $V_B + 0.3$	V
High-Side Floating Output Voltage	VHO	Vs - 0.3 to V <sub>B</sub> + 0.3	V
Offset Supply Voltage Transient	dVs/dt	50	V/ns
Low-Side Fixed Supply Voltage	Vcc	-0.3 to +24	V
Low-Side Output Voltage	VLO	-0.3 to Vcc + 0.3	V
Logic Input Voltage (HIN and LIN*)	Vin	-0.3 to Vcc + 0.3	V

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power-Dissipation Linear Derating Factor (Note 5)	PD	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	64	°C/W
Thermal Resistance, Junction to Case (Note 5)	Rejc	42	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	T∟	+300	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

# **Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply Absolute Voltage	V <sub>B</sub>	Vs + 10	V <sub>S</sub> + 20	V
High-Side Floating Supply Offset Voltage	Vs	(Note 6)	100	V
High-Side Floating Output Voltage	V <sub>HO</sub>	Vs	V <sub>B</sub>	V
Low-Side Fixed Supply Voltage	Vcc	10	20	V
Low-Side Output Voltage	V <sub>LO</sub>	0	Vcc	V
Logic-Input Voltage (HIN and LIN*)	$V_{IN}$	0	5	V
Ambient Temperature	TA	-40	+125	°C

Note: 6. Logic operation for  $V_S$  of -5V to +100V.



# DC Electrical Characteristics (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, @T<sub>A</sub> = +25°C, unless otherwise specified.) (Note 7)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" (HIN) & Logic "0" (LIN*) Input Voltage	VIH	2.5	-	-	V	Vcc = 10V to 20V
Logic "0" (HIN) & Logic "1" (LIN*) Input Voltage	VIL	_	1	0.8	V	Vcc = 10V to 20V
High-Level Output Voltage, VBIAS - VO	Vон	_	0.05	0.2	V	I <sub>O</sub> = 2mA
Low-Level Output Voltage, Vo	Vol	_	0.02	0.1	V	I <sub>O</sub> = 2mA
Offset Supply Leakage Current	ILK	_	1	50	μΑ	V <sub>B</sub> = V <sub>S</sub> = 100V
Quiescent V <sub>BS</sub> Supply Current	I <sub>BSQ</sub>	_	60	100	μΑ	VIN = 0V or 5V
Quiescent Vcc Supply Current	Iccq	_	350	500	μΑ	VIN = 0V or 5V
Logic "1" Input Bias Current	I <sub>IN+</sub>	_	3	10	μΑ	HIN = 5V, LIN* = 0V
Logic "0" Input Bias Current	I <sub>IN</sub> -	_	_	5.0	μΑ	HIN = 0V, LIN* = 5V
Vcc Supply Undervoltage Positive Going Threshold	Vccuv+	7.4	8.5	9.6	V	_
Vcc Supply Undervoltage Negative Going Threshold	Vccuv-	7.1	7.8	8.8	V	_
V <sub>BS</sub> Supply Undervoltage Positive Going Threshold	V <sub>BSUV+</sub>	5.5	6.5	7.5	V	_
V <sub>BS</sub> Supply Undervoltage Negative Going Threshold	V <sub>BSUV</sub> -	5.3	6.3	7.3	V	_
Output High Short-Circuit Pulsed Current	I <sub>O+</sub>	130	290	_	mA	V <sub>O</sub> = 0V, PW ≤ 10μs
Output Low Short-Circuit Pulsed Current	lo-	270	600	_	mA	V <sub>O</sub> = 15V, PW ≤ 10μs

Note:

# AC Electrical Characteristics (V<sub>BIAS</sub> (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, C<sub>L</sub> = 1000pF, @T<sub>A</sub> = +25°C, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-On Propagation Delay	ton	_	680	820	ns	Vs = 0V
Turn-Off Propagation Delay	toff	_	150	220	ns	Vs = 100V
Delay Matching, HO & LO Turn-On/Turn-Off	tьм	_	_	60	ns	_
Turn-On Rise Time	tR	_	70	170	ns	Vs = 0V
Turn-Off Fall Time	tF	_	35	90	ns	Vs = 0V
Deadtime: tpт Lo-нo & tpт нo-Lo	tот	300	430	550	ns	_

<sup>7.</sup> The  $V_{IN}$  and  $I_{IN}$  parameters are applicable to the two logic pins: HIN and LIN\*. The  $V_O$  and  $I_O$  parameters are applicable to the respective output pins: HO and LO.



# **Timing Waveforms**

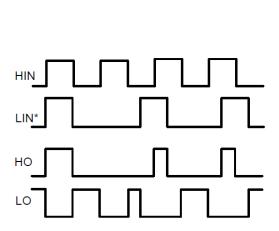


Figure 1. Input / Output Timing Diagram

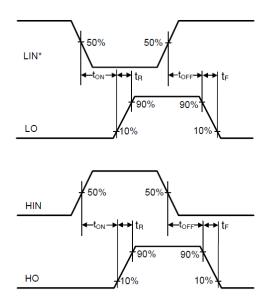


Figure 2. Switching Time Waveform Definitions

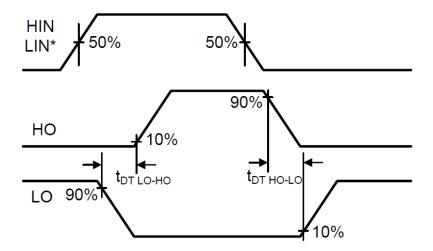


Figure 3. Deadtime Waveform Definitions



## Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.)

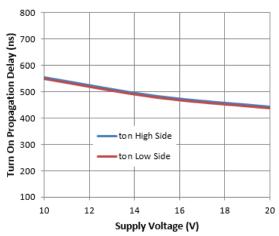


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

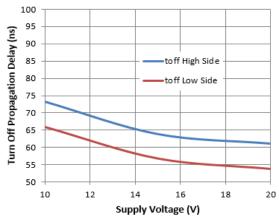


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

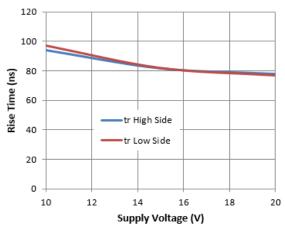


Figure 8. Rise Time vs. Supply Voltage

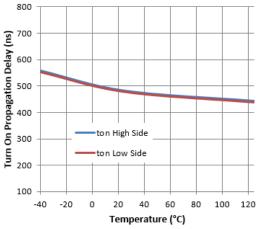


Figure 5. Turn-on Propagation Delay vs. Temperature

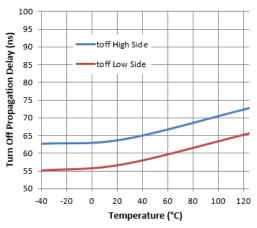


Figure 7. Turn-off Propagation Delay vs. Temperature

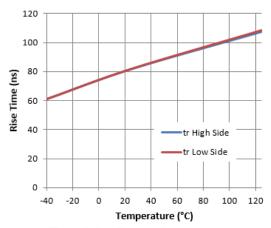


Figure 9. Rise Time vs. Temperature



## Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.) (continued)

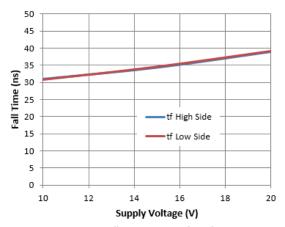


Figure 10. Fall Time vs. Supply Voltage

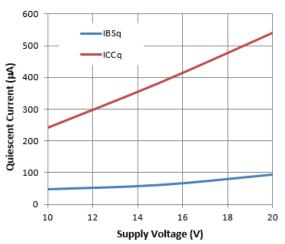


Figure 12. Quiescent Current vs. Supply Voltage

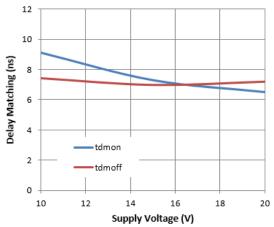


Figure 14. Delay Matching vs. Supply Voltage

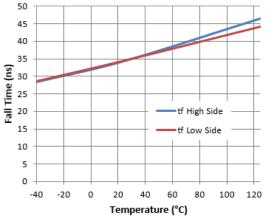


Figure 11. Fall Time vs. Temperature

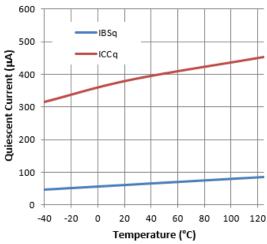


Figure 13. Quiescent Current vs. Temperature

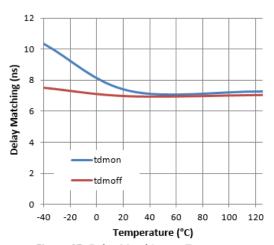


Figure 15. Delay Matching vs. Temperature



# Typical Performance Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.) (continued)

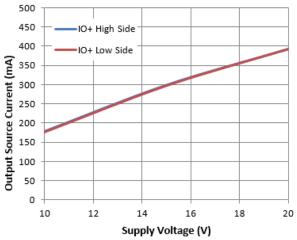


Figure 16. Output Source Current vs. Supply Voltage

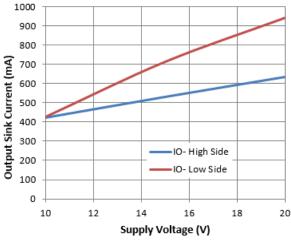


Figure 18. Output Sink Current vs. Supply Voltage

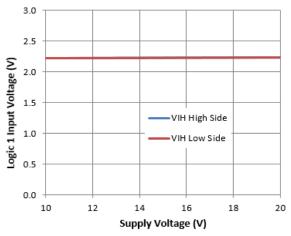


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

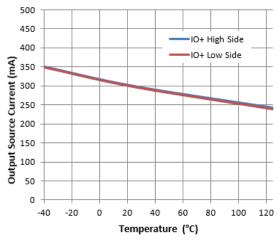


Figure 17. Output Source Current vs. Temperature

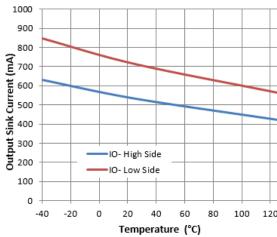


Figure 19. Output Sink Current vs. Temperature

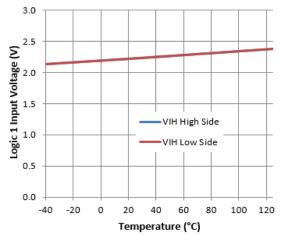


Figure 21. Logic 1 Input Voltage vs. Temperature



## Typical Performance Characteristics (@TA = +25°C, unless otherwise specified.) (continued)

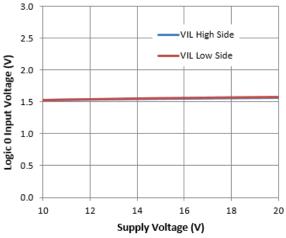


Figure 22. Logic O Input Voltage vs. Supply Voltage

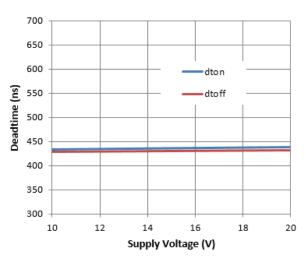


Figure 24. Deadtime vs. Supply Voltage

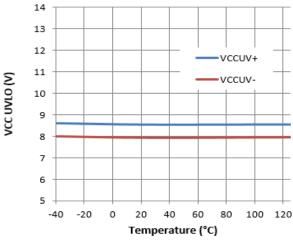


Figure 26. VCC UVLO vs. Temperature

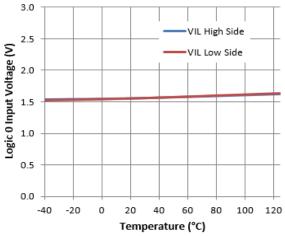


Figure 23. Logic 0 Input Voltage vs. Temperature

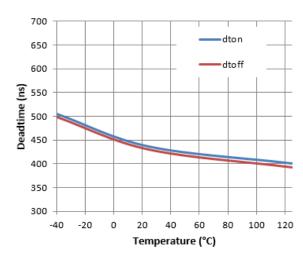


Figure 25. Deadtime vs. Temperature

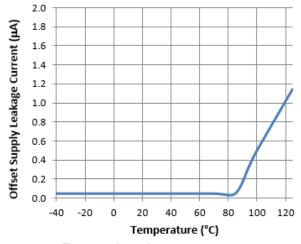


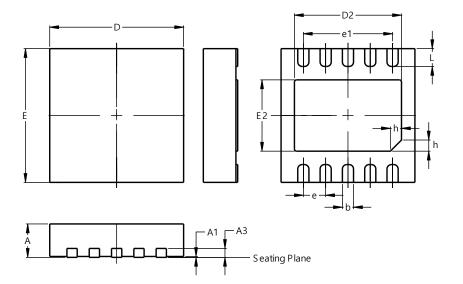
Figure 27. Offset Supply Leakage Current vs. Temperature



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### W-DFN3030-10 (Type TH)

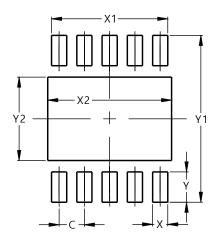


W-DFN3030-10						
(Type TH)						
Dim	Min Max Typ					
Α	0.70	0.80	0.75			
A1	-	0.05	0.02			
A3	0.18	0.25	0.20			
b	0.18	0.30	0.25			
D	2.90	3.10	3.00			
D2	2.40	2.60	2.50			
е	0.50BSC					
e1	2.00BSC					
Е	2.90	3.10	3.00			
E2	1.45	1.65	1.55			
h	0.20	0.30	0.25			
L	0.30	0.50	0.40			
All Dimensions in mm						

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### W-DFN3030-10 (Type TH)



Dimensions	Value			
<b>D</b>	(in mm)			
C	0.500			
X	0.300			
X1	2.300			
X2	2.600			
Υ	0.600			
Y1	3.300			
Y2	1.650			

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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DGD0503

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